

**1993 International Workshop on VLSI Process and
Device Modeling (1993 VPAD)**

May 14 (Fri.) - May 15 (Sat.), 1993
Nara Ken - New Public Hall , Nara , Japan

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IEEE Electron Devices Society
In cooperation with : IEEE Asian Steering Committee for Trans. on CAD/ICAS
Institute of Electronics, Information and
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	T. Wada(Toshiba Corp.)

VPAD 93 Time Schedule

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T. Toyabe, Hitachi Ltd.

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K. Nishi(Oki Electric Ind. Co., Ltd.)

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A. Strojwas(Carnegie Mellon Univ.)

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D. Scharfetter, Intel Corp.

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M. Tomizawa, NTT Corp.

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